

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	293	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:21
L2	1268	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:21
L3	4	1 and L2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:21
L4	0	L3 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:21
L5	70	L1 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:23
L6	31536	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:23
L7	21	L1 and L6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:23

L8	6	I7 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:23
S1	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 20:39
S2	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:07
S3	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:10
S4	1268	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:15
S5	83939	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:19
S6	155	S4 and S5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:19
S7	17	S6 and (AlN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:20

S8	7	S7 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:22
S9	22	S6 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:24
S10	9	S9 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:24
S11	80	S6 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:28
S12	11	S11 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:30
S13	25	("3692700" "4849797" "5107315" "5135885" "5184199" "5258631" "5326992" "5382822" "5539217" "5597744" "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/21 21:38
S14	43235	(AIN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:46
S15	42515	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:46

S16	111	S4 and S15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:47
S17	61	S16 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:47
S18	1628	(AlN or (Aluminum near nitride)) same ("SiO. sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:49
S19	32	S4 and S18	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:49
S20	22	S19 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:49
S21	696	S18 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 22:01
S22	9117	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 22:04
S23	39	S21 and S22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 22:04

S24	412	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 22:19
S25	125	S24 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 22:20
S26	1268	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 01:37
S27	42515	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 01:37
S28	111	S26 and S27	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 01:37
S29	61	S28 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 01:37
S30	4	S29 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 01:37
S31	901	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:29

S32	402	S31 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:30
S33	845	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:31
S34	381	S33 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:31
S35	40	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:32
S36	15	S35 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:32
S37	84	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non- volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:36
S38	23	S37 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:36
S39	239	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:37

S40	90	S39 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:38
S41	7	257/314.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:24
S42	105	257/76.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:25
S43	140	257/77.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:25
S44	22	257/410.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:25
S45	35	257/613.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:25
S46	3	257/629.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:25
S47	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:42

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